

JVSTB

Journal of Vacuum Science & Technology B | 2nd Series | Volume 31, Number 3 | May/June 2013

Nanotechnology and Microelectronics: Materials, Processing, Measurement, and Phenomena

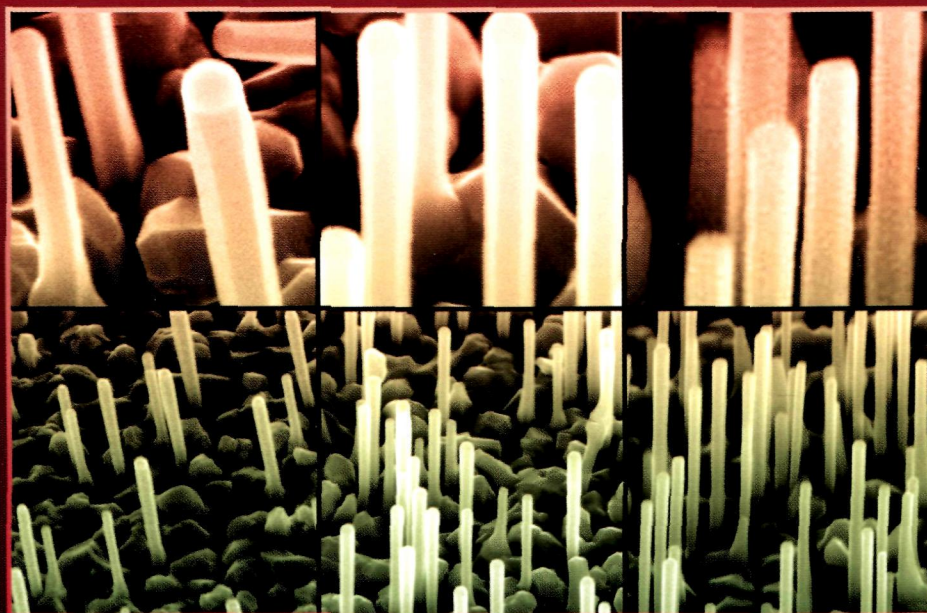


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Papers from the 29th North American Conference on Molecular Beam Epitaxy



An AVS journal published by the Society
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Nanotechnology and Microelectronics:

Materials, Processing, Measurement, and Phenomena

Second Series
Volume 31, Number 3
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Journal of Vacuum Science & Technology B Nanotechnology and Microelectronics: Materials, Processing, Measurement and Phenomena (ISSN: 0734-211X) is published six times annually (Jan/Feb, Mar/Apr, May/Jun, Jul/Aug, Sep/Oct, Nov/Dec) by AVS through AIP Publishing LLC, Suite 1N01, 2 Huntington Quadrangle, Melville, NY 11747-4502. Periodicals postage paid at Huntington Station, NY 11746, and at additional mailing offices. 2013 subscription rates are: US \$1720. POSTMASTER: Send address changes to *Journal of Vacuum Science & Technology B Nanotechnology and Microelectronics: Materials, Processing, Measurement and Phenomena*, Membership Services, AVS, 125 Maiden Lane, 15th Floor, New York, NY 10038, membership@avs.org, www.avs.org.

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Saumya Sengupta, Arjun Mandal, Hemant Ghadi, Subhananda Chakrabarti, and Keshav Lal Mathur.....

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On The Cover: *Supanee Sukritanon, YanJin Kuang, Charles W. Tu, JVST B, 31(3), p. 03C110-3 (2013). Cover shows SEM images of GaP Nanowires on Si(111), which have a growth window from ~585 °C to ~615 °C.*